

# NLAS4684

## Ultra-Low Resistance Dual SPDT Analog Switch

The NLAS4684 is an advanced CMOS analog switch fabricated in Sub-micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra-Low  $R_{ON}$  of  $0.5\ \Omega$ , for the Normally Closed (NC) switch, and  $0.8\ \Omega$  for the normally closed switch (NO) at 2.7 V.

The part also features guaranteed Break Before Make switching, assuring the switches never short the driver.

The NLAS4684 is available in a  $2.0 \times 1.5$  mm bumped die array, with a  $3 \times 4$  arrangement of solder bumps. The pitch of the solder bumps is 0.5 mm for easy handling.

### Features

- Ultra-Low  $R_{ON}$ ,  $< 0.5\ \Omega$  at 2.7 V
- Threshold Adjusted to Function with 1.8 V Control at  $V_{CC} = 2.7\text{--}3.3$  V
- Single Supply Operation from 1.8-5.5 V
- Tiny  $2 \times 1.5$  mm Bumped Die
- Low Crosstalk,  $< 83$  dB at 100 kHz
- Full  $0\text{--}V_{CC}$  Signal Handling Capability
- High Isolation,  $-65$  dB at 100 kHz
- Low Standby Current,  $< 50$  nA
- Low Distortion,  $< 0.14\%$  THD
- $R_{ON}$  Flatness of  $0.15\ \Omega$
- Pin for Pin Replacement for MAX4684

### Applications

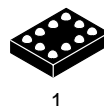
- Cell Phone
- Speaker Switching
- Power Switching (Up to 100 mA)
- Modems
- Automotive



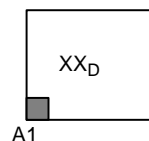
ON Semiconductor®

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### MARKING DIAGRAM

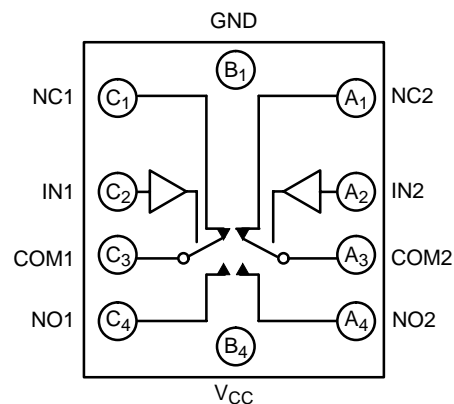


Microbump-10  
CASE 489AA



XX = Device Code  
D = Date Code

### PIN CONNECTIONS AND LOGIC DIAGRAM



### FUNCTION TABLE

IN 1, 2	NO 1, 2	NC 1, 2
0	OFF	ON
1	ON	OFF

### ORDERING INFORMATION

Device	Package	Shipping
NLAS4684	Microbump-10	3000/Tape & Reel

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage	− 0.5 to +7.0	V
V <sub>IS</sub>	Analog Input Voltage (V <sub>NO</sub> , V <sub>NC</sub> , or V <sub>COM</sub> ) (Note 1)	− 0.5 ≤ V <sub>IS</sub> ≤ V <sub>CC</sub> + 0.5	V
V <sub>IN</sub>	Digital Select Input Voltage	− 0.5 ≤ V <sub>I</sub> ≤ +7.0	V
I <sub>IK</sub>	DC Current, Into or Out of Any Pin	± 50	mA

1. Signal voltage on NC, NO, and COM exceeding V<sub>CC</sub> or GND are clamped by the internal diodes. Limit forward diode current to maximum current rating.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	1.8	5.5	V
V <sub>IN</sub>	Digital Select Input Voltage	GND	5.5	V
V <sub>IS</sub>	Analog Input Voltage (NC, NO, COM)	GND	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range	− 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time, SELECT V <sub>CC</sub> = 3.3 V ± 0.3 V V <sub>CC</sub> = 5.0 V ± 0.5 V	0 0	100 20	ns/V

## DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V <sub>CC</sub> ± 10%	Guaranteed Limit			Unit
				− 55°C to 25°C	< 85°C	< 125°C	
V <sub>IH</sub>	Minimum High- Level Input Voltage, Select Inputs (Figure 7)		2.0	1.4	1.4	1.4	V
			2.5	1.4	1.4	1.4	
			3.0	1.4	1.4	1.4	
			5.0	2.0	2.0	2.0	
V <sub>IL</sub>	Maximum Low- Level Input Voltage, Select Inputs (Figure 7)		2.0	0.5	0.5	0.5	V
			2.5	0.5	0.5	0.5	
			3.0	0.5	0.5	0.5	
			5.0	0.8	0.8	0.8	
I <sub>IN</sub>	Maximum Input Leakage Current, Select Inputs	V <sub>IN</sub> = 5.5 V or GND	5.5	± 1.0	± 1.0	± 1.0	μA
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0	± 10	± 10	± 10	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	Select and V <sub>IS</sub> = V <sub>CC</sub> or GND	5.5	± 50	± 200	± 200	nA

DC ELECTRICAL CHARACTERISTICS - Analog Section

Symbol	Parameter	Condition	V <sub>CC</sub> ± 10%	Guaranteed Maximum Limit						Unit
				-55 °C to 25°C		< 85°C		< 125°C		
				Min	Max	Min	Max	Min	Max	
R <sub>ON</sub> (NC)	NC “ON” Resistance (Note 2)	V <sub>IN</sub> ≤ V <sub>IL</sub>	2.5		0.6		0.7		0.8	Ω
		V <sub>IS</sub> = GND to V <sub>CC</sub>	3.0		0.5		0.5		0.5	
		I <sub>IN</sub> ≤ 100 mA	5.0		0.4		0.4		0.5	
R <sub>ON</sub> (NO)	NO “ON” Resistance (Note 2)	V <sub>IN</sub> ≥ V <sub>IH</sub>	2.5		2.0		2.0		2.0	Ω
		V <sub>IS</sub> = GND to V <sub>CC</sub>	3.0		0.8		0.8		1.0	
		I <sub>IN</sub> ≤ 100 mA	5.0		0.8		0.8		0.9	
R <sub>FLAT</sub> (NC)	NC_On-Resistance Flatness (Notes 2, 4)	I <sub>COM</sub> = 100 mA	2.5		0.15		0.15		0.15	Ω
		V <sub>IS</sub> = 0 to V <sub>CC</sub>	3.0		0.15		0.15		0.15	
			5.0		0.15		0.15		0.15	
R <sub>FLAT</sub> (NO)	NO_On-Resistance Flatness (Notes 2, 4)	I <sub>COM</sub> = 100 mA	2.5		0.35		0.35		0.35	Ω
		V <sub>IS</sub> = 0 to V <sub>CC</sub>	3.0		0.35		0.35		0.35	
			5.0		0.35		0.35		0.35	
ΔR <sub>ON</sub>	On-Resistance Match Between Channels (Notes 2 and 3)	V <sub>IS</sub> = 1.3 V; I <sub>COM</sub> = 100 mA	2.5		0.18		0.18		0.18	Ω
		V <sub>IS</sub> = 1.5 V; I <sub>COM</sub> = 100 mA	3.0		0.06		0.06		0.06	
		V <sub>IS</sub> = 2.8 V; I <sub>COM</sub> = 100 mA	5.0		0.06		0.06		0.06	
I <sub>NC(OFF)</sub> I <sub>NO(OFF)</sub>	NC or NO Off Leakage Current (Figure 10)	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>NO</sub> or V <sub>NC</sub> = 1.0 V <sub>COM</sub> = 4.5 V	5.5	-1	1	-10	10	-100	100	nA
I <sub>COM(ON)</sub>	COM ON Leakage Current (Figure 10)	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>NO</sub> 1.0 V or 4.5 V with V <sub>NC</sub> floating or V <sub>NC</sub> 1.0 V or 4.5 V with V <sub>NO</sub> floating V <sub>COM</sub> = 1.0 V or 4.5 V	5.5	-1	1	-10	10	-100	100	nA

2. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
3.  $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$  between NC1 and NC2 or between NO1 and NO2.
4. Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r = t_f = 3.0$  ns)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> (V)	V <sub>IS</sub> (V)	Guaranteed Maximum Limit						Unit	
					– 55°C to 25°C			< 85°C		< 125°C		
					Min	Typ*	Max	Min	Max	Min		Max
t <sub>ON</sub>	Turn-On Time	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 35 pF (Figures 2 and 3)	2.5 3.0 5.0	1.3 1.5 2.8			60 50 30		70 60 35		70 60 35	ns
t <sub>OFF</sub>	Turn-Off Time	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 35 pF (Figures 2 and 3)	2.5 3.0 5.0	1.3 1.5 2.8			50 40 30		55 50 35		55 50 35	ns
t <sub>BBM</sub>	Minimum Break- Before- Make Time	V <sub>IS</sub> = 3.0 R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF (Figure 1)	3.0	1.5	2	15						ns

		Typical @ 25, V <sub>CC</sub> = 5.0 V	pF
C <sub>NC</sub> Off	NC Off Capacitance, f = 1 MHz	102	
C <sub>NO</sub> Off	NO Off Capacitance, f = 1 MHz	104	
C <sub>NC</sub> On	NC On Capacitance, f = 1 MHz	322	
C <sub>NO</sub> Off	NO On Capacitance, f = 1 MHz	330	

\*Typical Characteristics are at 25°C.

**ADDITIONAL APPLICATION CHARACTERISTICS** (Voltages Referenced to GND Unless Noted) (Note 6)

Symbol	Parameter	Condition	$V_{CC}$ V	Typical	Unit
				25°C	
BW	Maximum On-Channel -3dB Bandwidth or Minimum Frequency Response	$V_{IN} = 0$ dBm $V_{IN}$ centered between $V_{CC}$ and GND (Figure 4)	NC 3.0	6.5 9.5	MHz
$V_{ONL}$	Maximum Feedthrough On Loss	$V_{IN} = 0$ dBm @ 100 kHz to 50 MHz $V_{IN}$ centered between $V_{CC}$ and GND (Figure 4)	3.0	-0.05	dB
$V_{ISO}$	Off-Channel Isolation	f = 100 kHz; $V_{IS} = 1$ V RMS; $C_L = 5$ nF $V_{IN}$ centered between $V_{CC}$ and GND (Figure 4)	3.0	-93	dB
Q	Charge Injection Select Input to Common I/O (Figures 7 and 8)	$V_{IN} = V_{CC}$ to GND, $R_{IS} = 0 \Omega$ , $C_L = 1$ nF $Q = C_L \cdot \Delta V_{OUT}$ (Figure 5)	3.0	20	pC
THD	Total Harmonic Distortion THD + Noise (Figure 6)	$F_{IS} = 20$ Hz to 100 kHz, $R_L = R_{gen} = 600 \Omega$ , $C_L = 50$ pF $V_{IS} = 1$ V RMS	3.0	0.14	%
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; $V_{IS} = 1$ V RMS, $C_L = 5$ pF, $R_L = 50 \Omega$ $V_{IN}$ centered between $V_{CC}$ and GND (Figure 4)	3.0	-83	dB

5. Off-Channel Isolation =  $20 \log_{10} (V_{com}/V_{no})$ ,  $V_{com}$  = output,  $V_{no}$  = input to off switch.

6. -40 °C specifications are guaranteed by design.

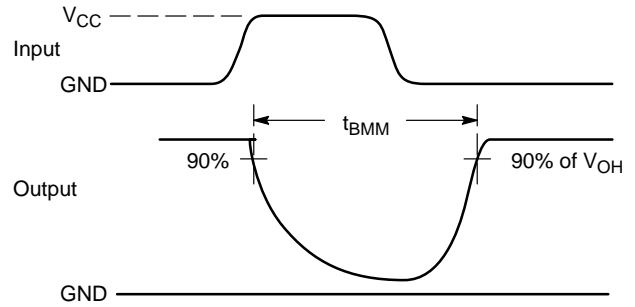
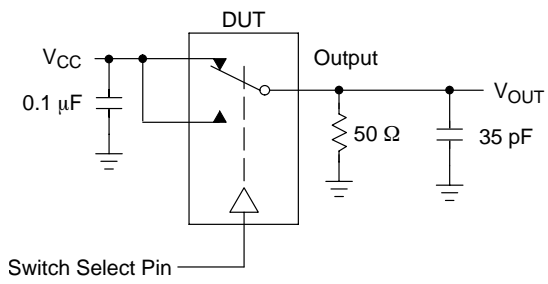


Figure 1.  $t_{BMM}$  (Time Break-Before-Make)

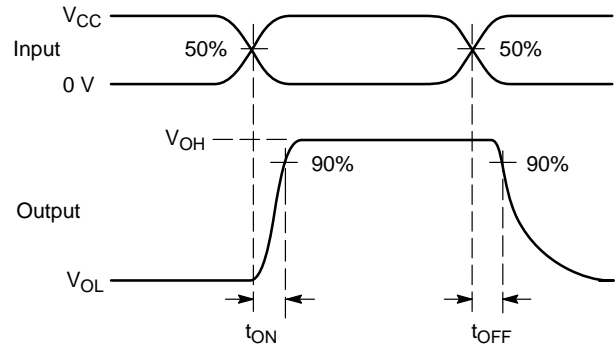
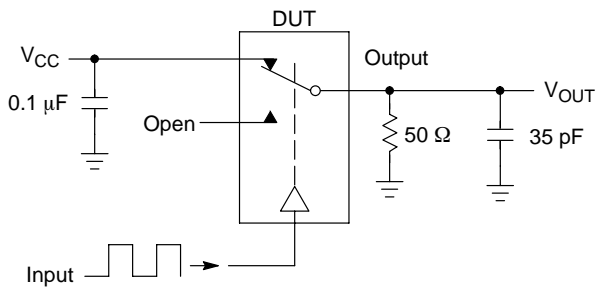


Figure 2.  $t_{ON}/t_{OFF}$

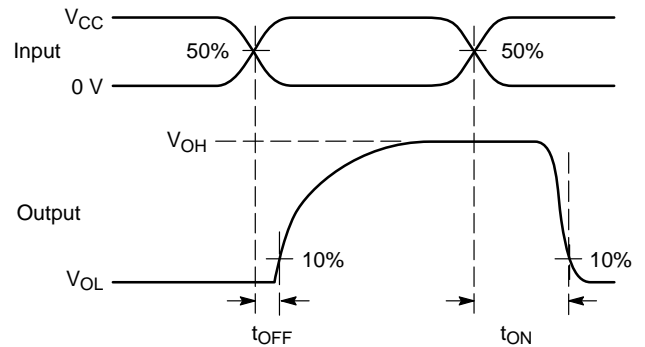
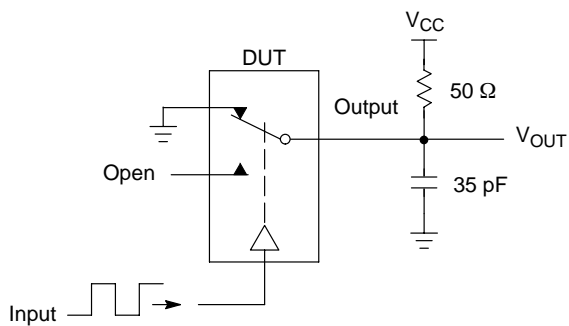
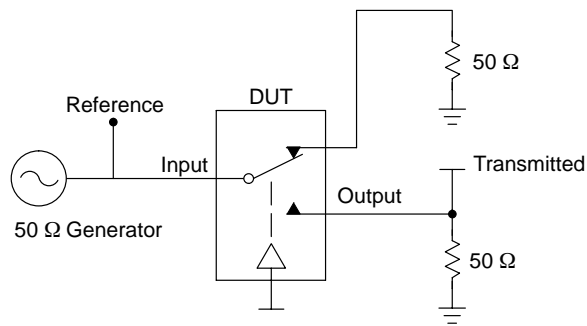


Figure 3.  $t_{ON}/t_{OFF}$



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch.  $V_{ISO}$ , Bandwidth and  $V_{ONL}$  are independent of the input signal direction.

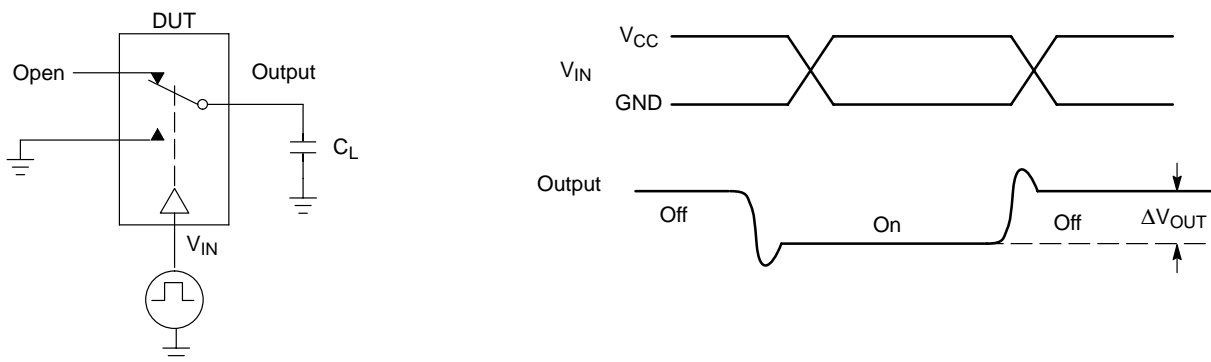
$$V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log } \left( \frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz}$$

$$V_{ONL} = \text{On Channel Loss} = 20 \text{ Log } \left( \frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz}$$

Bandwidth (BW) = the frequency 3 dB below  $V_{ONL}$

$V_{CT}$  = Use  $V_{ISO}$  setup and test to all other switch analog input/outputs terminated with 50 Ω

**Figure 4. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ $V_{ONL}$**



**Figure 5. Charge Injection: (Q)**

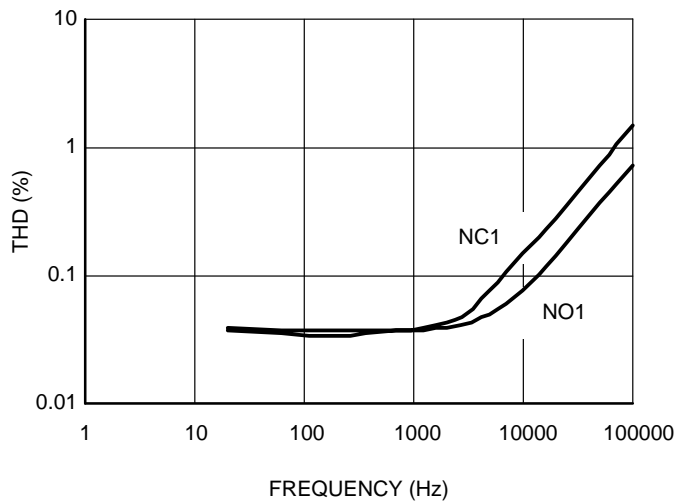


Figure 6. Total Harmonic Distortion Plus Noise Versus Frequency

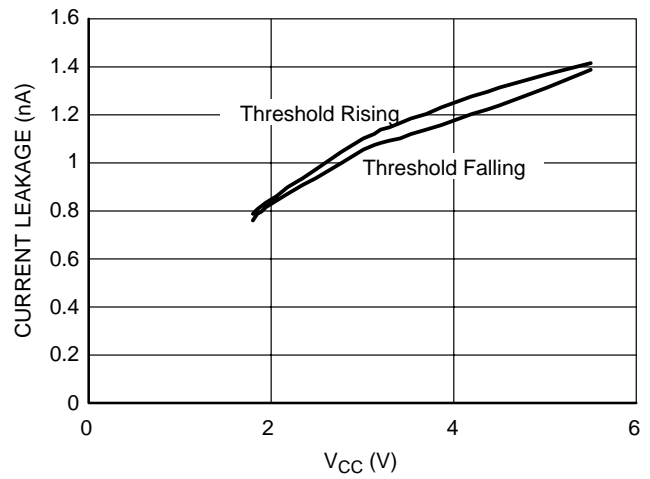


Figure 7. Voltage in Threshold on Logic Pins

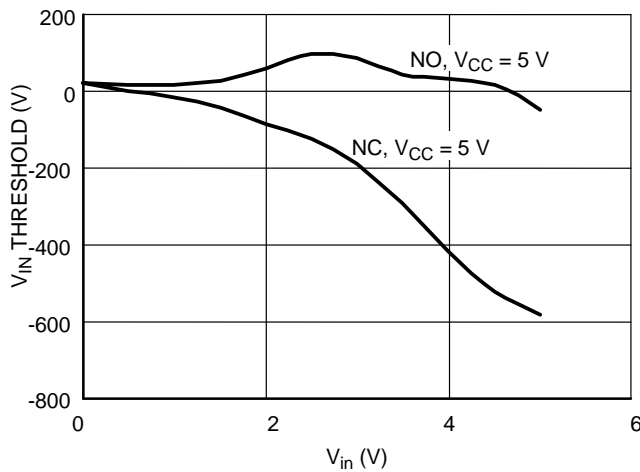


Figure 8. Charge Injection versus  $V_{IS}$

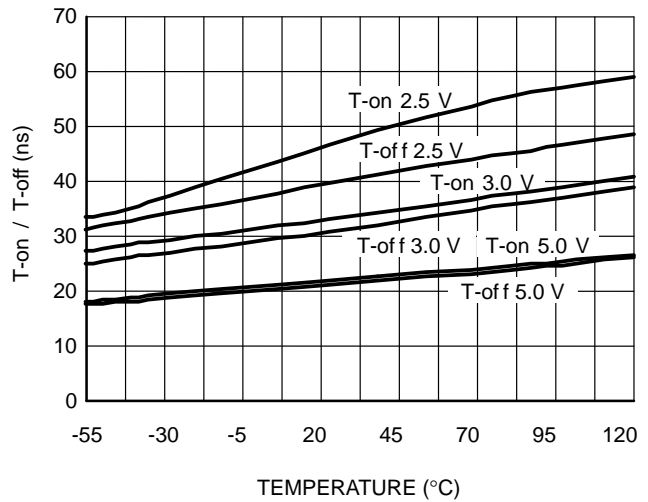


Figure 9. T-on / T-off Time versus Temperature

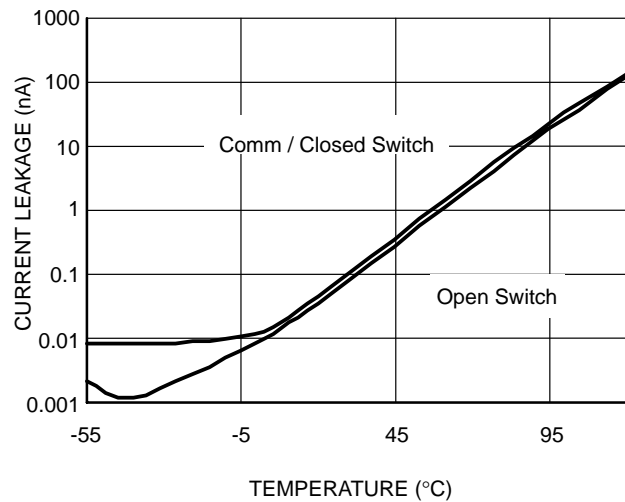


Figure 10. NO/NC Current Leakage Off and On,  $V_{CC} = 5 V$

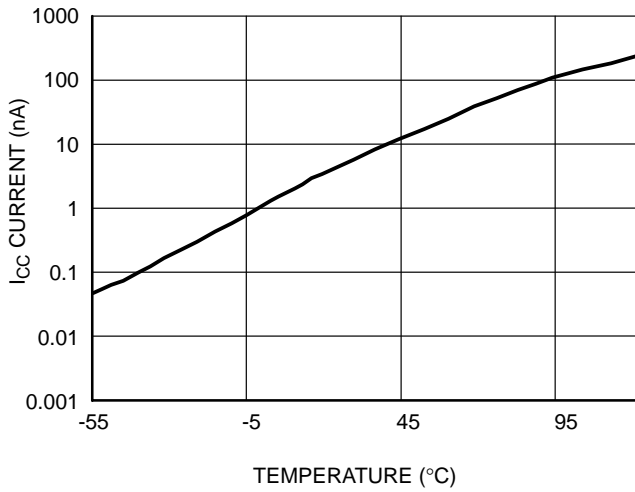


Figure 11.  $I_{CC}$  Current Leakage versus Temperature  $V_{CC} = 5.5$  V

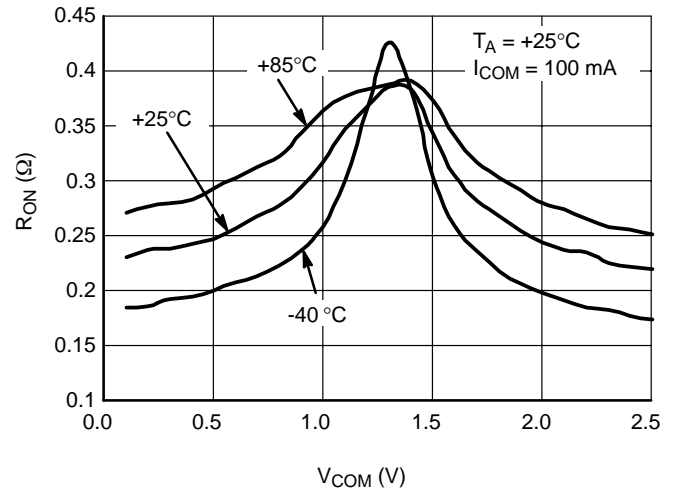


Figure 12. NC On-Resistance versus COM Voltage

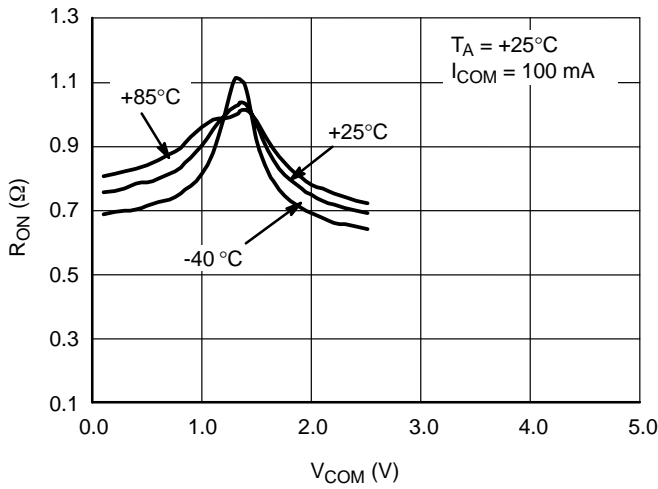


Figure 13. NO On-Resistance versus COM Voltage

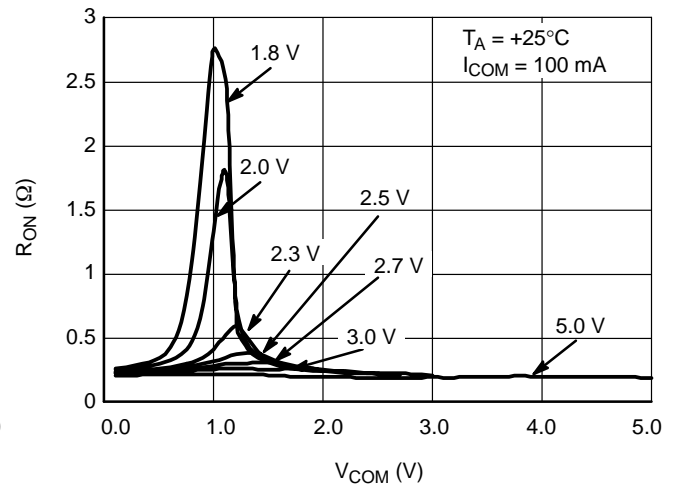


Figure 14. NC On-Resistance versus COM Voltage

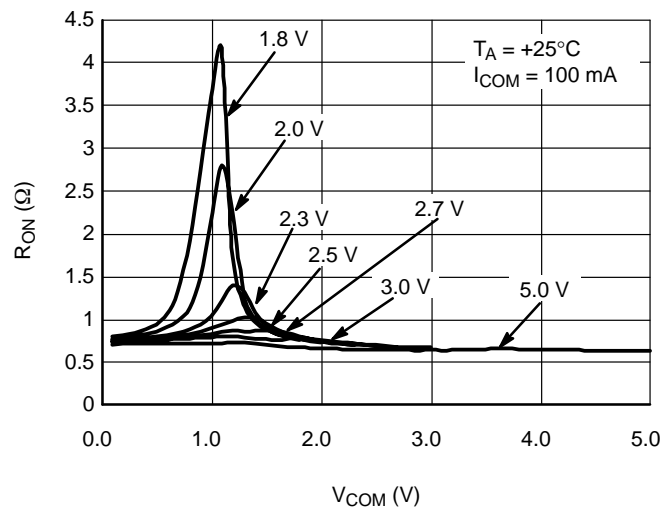


Figure 15. NO On-Resistance versus COM Voltage



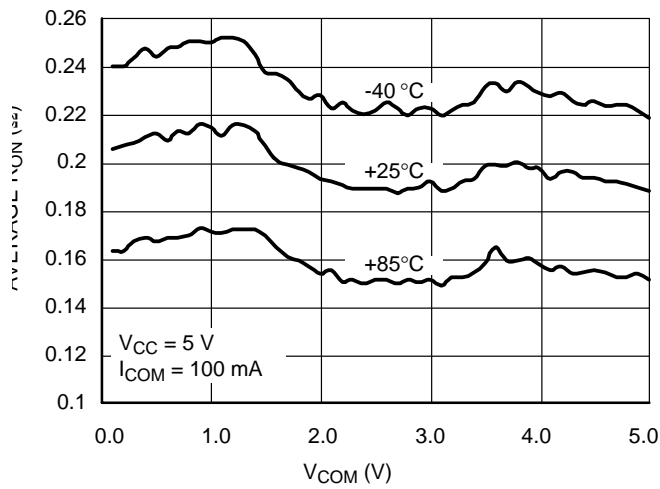


Figure 16. NC On-Resistance versus COM Voltage

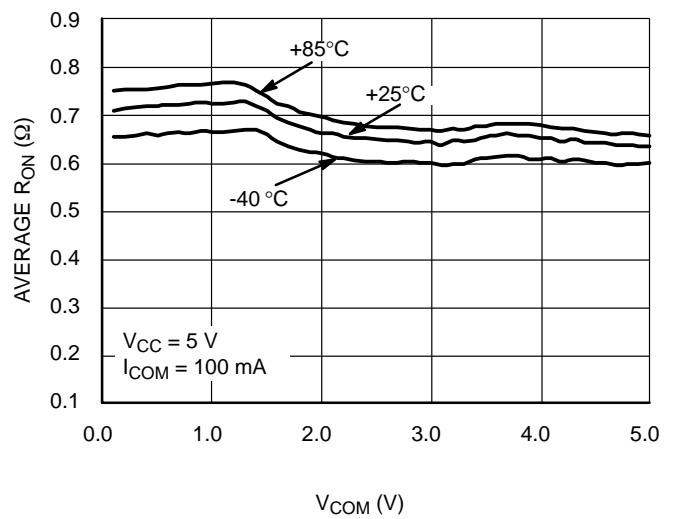


Figure 17. NO On-Resistance versus COM Voltage

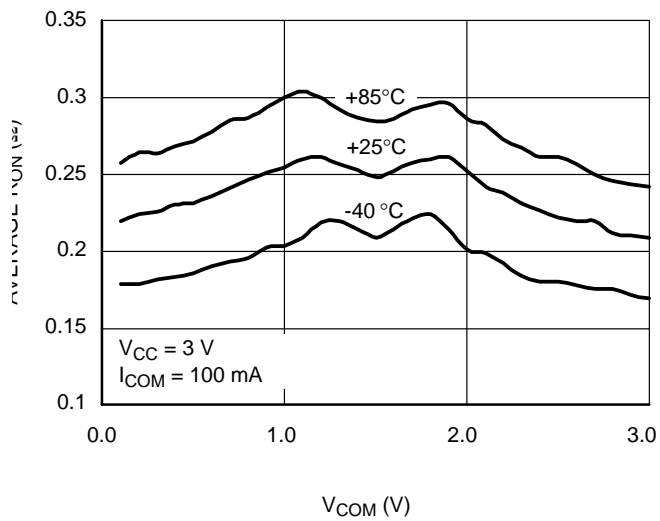


Figure 18. NC On-Resistance versus COM Voltage

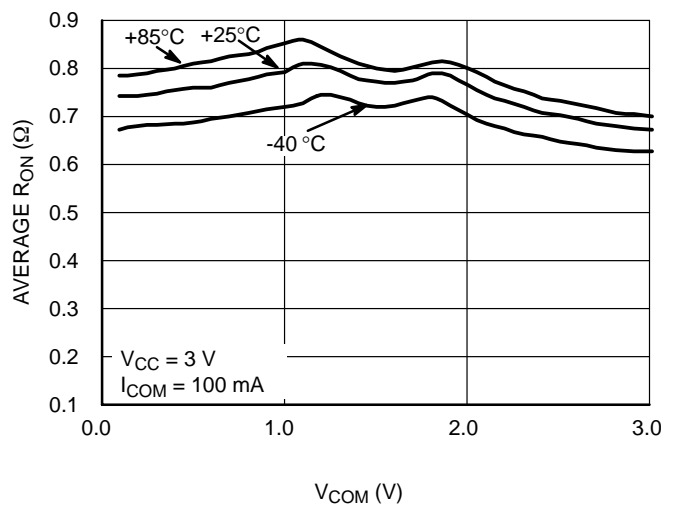


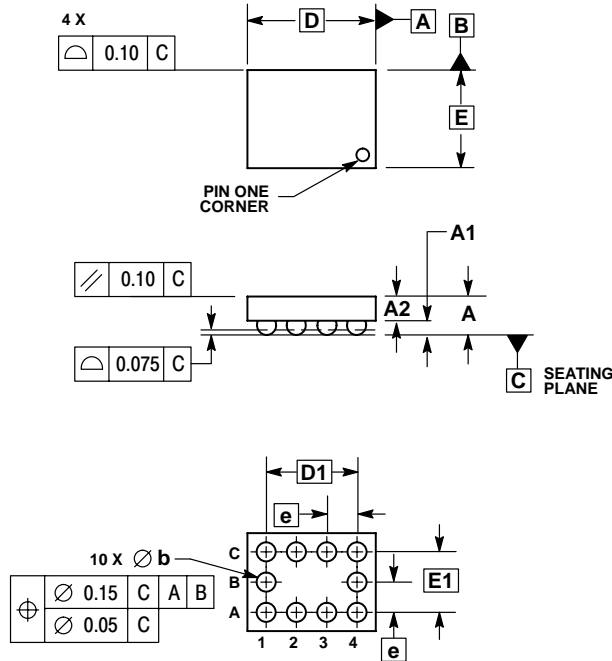
Figure 19. NO On-Resistance versus COM Voltage

## PACKAGE DIMENSIONS


**Microbump-10**  
CASE 489AA-01  
ISSUE O

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.



MILLIMETERS		
DIM	MIN	MAX
A	---	0.650
A1	0.210	0.270
A2	0.280	0.380
D	1.965 BSC	
E	1.465 BSC	
b	0.250	0.350
e	0.500 BSC	
D1	1.500 BSC	
E1	1.000 BSC	

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